

# MOSFET – N-Channel, UniFET™, FRFET®

500 V, 24 A, 200 mΩ

## FDA24N50F

### Description

UniFET MOSFET is onsemi's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET MOSFET has been enhanced by lifetime control. Its trr is less than 100 ns and the reverse dv/dt immunity is 15 V/ns while normal planar MOSFETs have over 200 ns and 4.5 V/ns respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

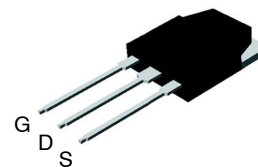
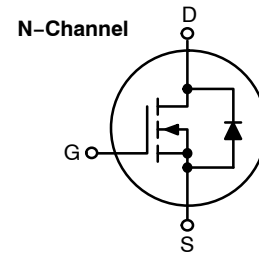
### Features

- $R_{DS(on)} = 166 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 12 \text{ A}$
- Low Gate Charge (Typ. 65 nC)
- Low  $C_{rss}$  (Typ. 32 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

### Applications

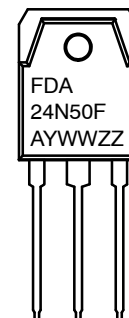
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

$V_{DS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
500 V	200 mΩ @ 10 V	24 A



TO-3P-3LD / EIAJ SC-65, ISOLATED  
CASE 340BZ

### MARKING DIAGRAM



FDA24N50F = Specific Device Code  
A = Assembly Site  
YWW = Date Code (Year & Work Week)  
ZZ = Assembly Lot Number

### ORDERING INFORMATION

Device	Package	Shipping
FDA24N50F	TO-3P-3LD	450 Units / Tube

# FDA24N50F

## MOSFET MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{DSS}$	Drain to Source Voltage		500	V
$V_{GSS}$	Gate to Source Voltage		$\pm 30$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	24	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	14	
		- Pulsed (Note 1)	96	
$I_{DM}$				
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)		1872	mJ
$I_{AR}$	Avalanche Current (Note 1)		24	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)		27	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ (Note 3)		20	V/ns
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	270	W
		-Derate above $= 25^\circ\text{C}$	2.2	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 6.5\text{ mH}$ ,  $I_{AS} = 24\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 24\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.46	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

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## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25°C	500	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25°C	–	0.6	–	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	–	–	1	μA
		V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C	–	–	10	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	3.0	–	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	–	0.166	0.200	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 12 A	–	30	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	3240	4310	pF
C <sub>oss</sub>	Output Capacitance		–	450	600	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	32	48	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 24 A, V <sub>GS</sub> = 10 V (Note 4)	–	65	85	nC
Q <sub>gs</sub>	Gate to Source Gate Charge		–	18	–	nC
Q <sub>gd</sub>	Gate to Drain “Miller” Charge		–	26	–	nC

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 24 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 25 Ω (Note 4)	–	49	108	ns
t <sub>r</sub>	Turn-On Rise Time		–	105	220	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	165	340	ns
t <sub>f</sub>	Turn-Off Fall Time		–	87	185	ns

### DRAIN-SOURCE DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		–	–	24	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		–	–	96	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 24 A	–	–	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 24 A, dI <sub>F</sub> /dt = 100 A/μs	–	264	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	1.4	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

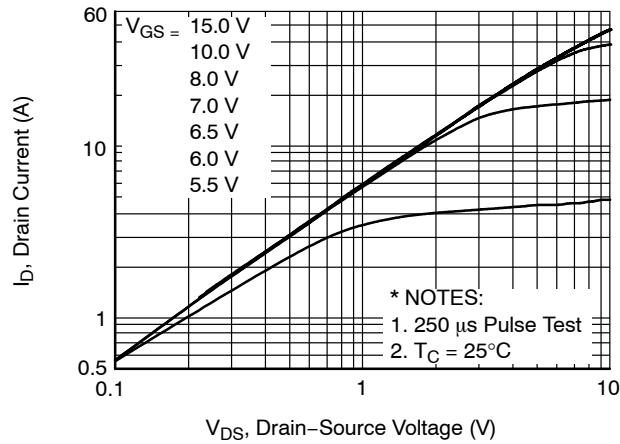


Figure 1. On-Region Characteristics

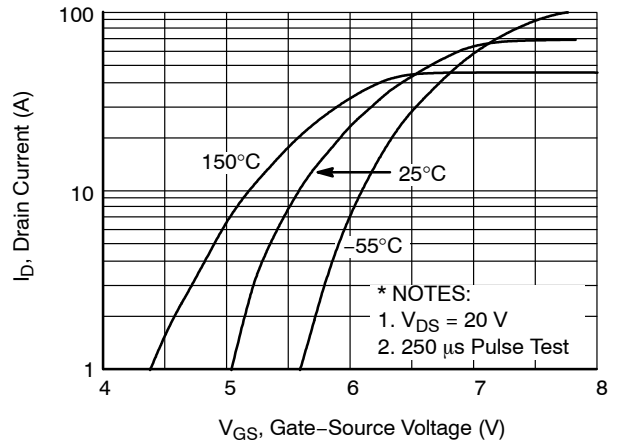


Figure 2. Transfer Characteristics

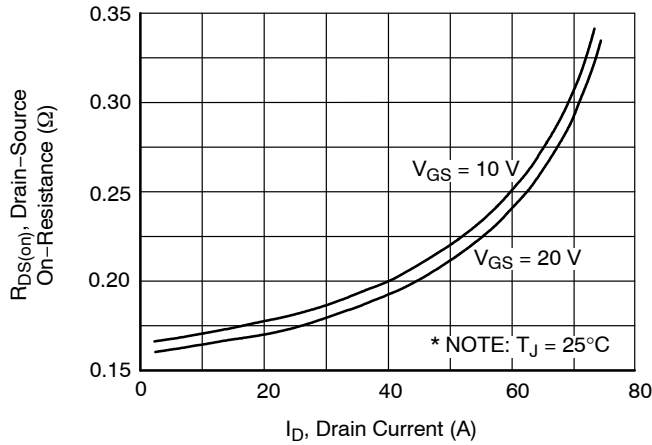


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

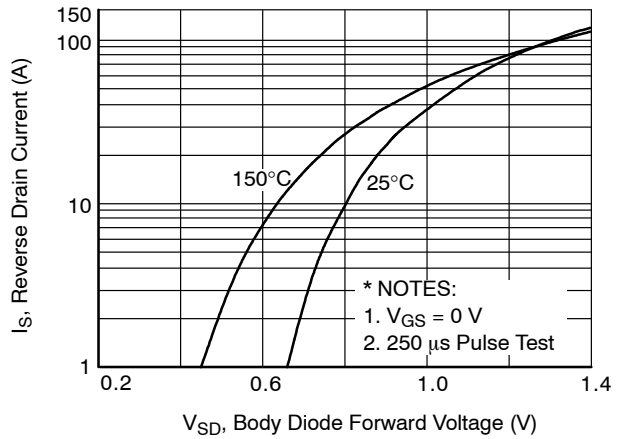


Figure 4. Body Diode Forward Voltage Variation vs. Source Current And Temperature

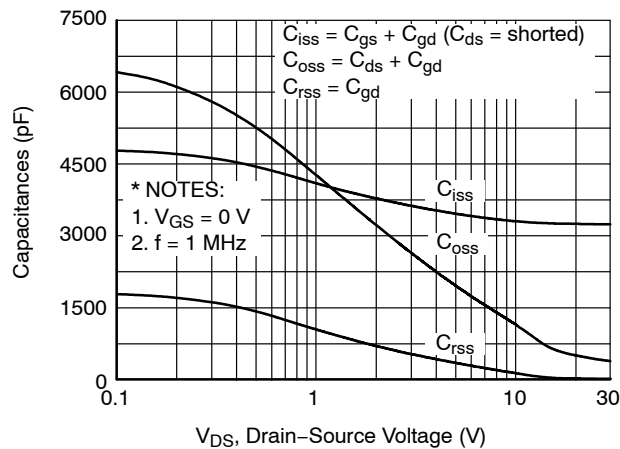


Figure 5. Capacitance Characteristics

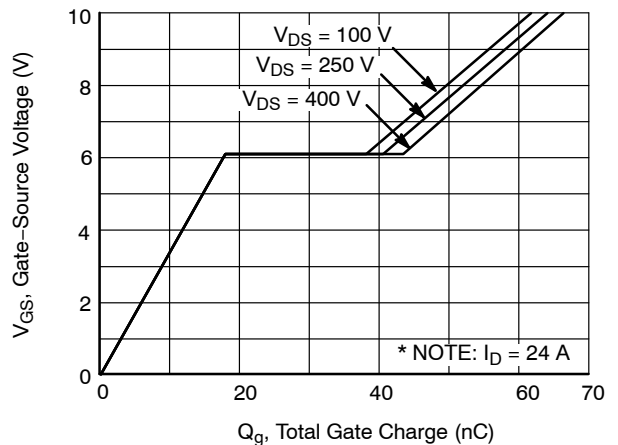


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

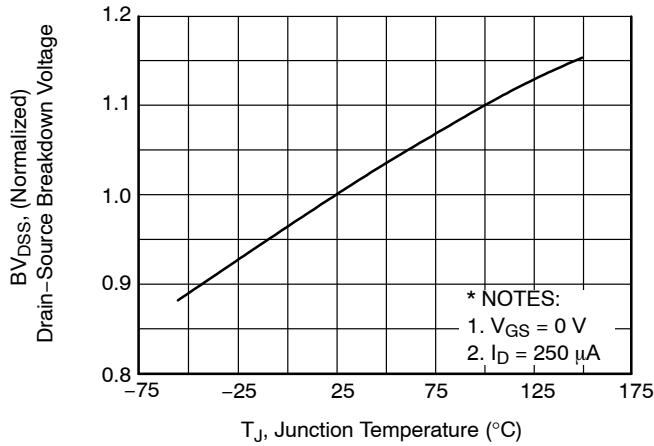


Figure 7. Breakdown Voltage Variation vs. Temperature

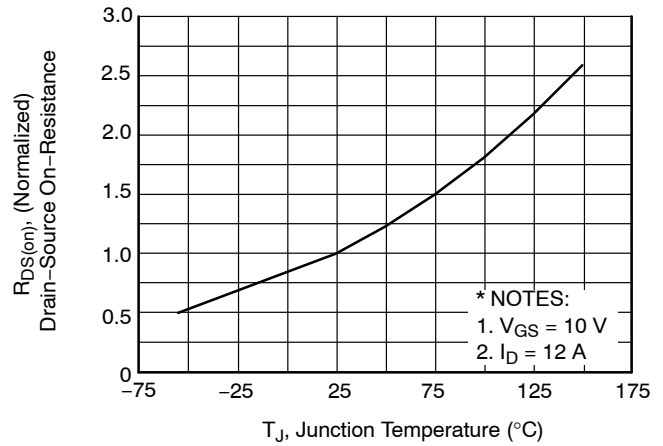


Figure 8. On-Resistance Variation vs. Temperature

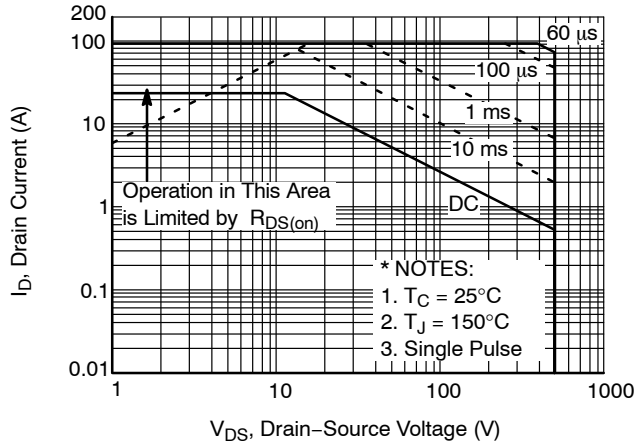


Figure 9. Maximum Safe Operating Area

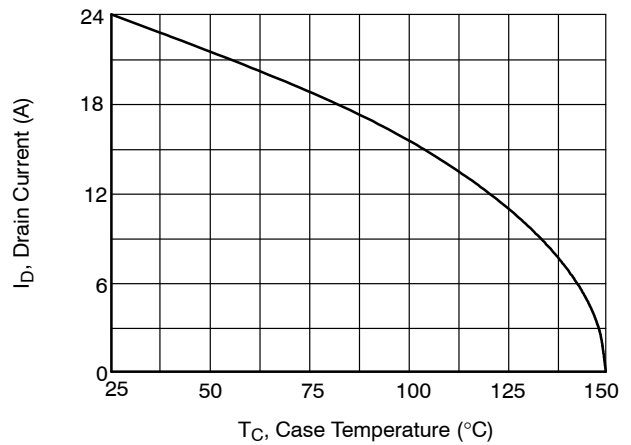


Figure 10. Maximum Drain Current vs. Case Temperature

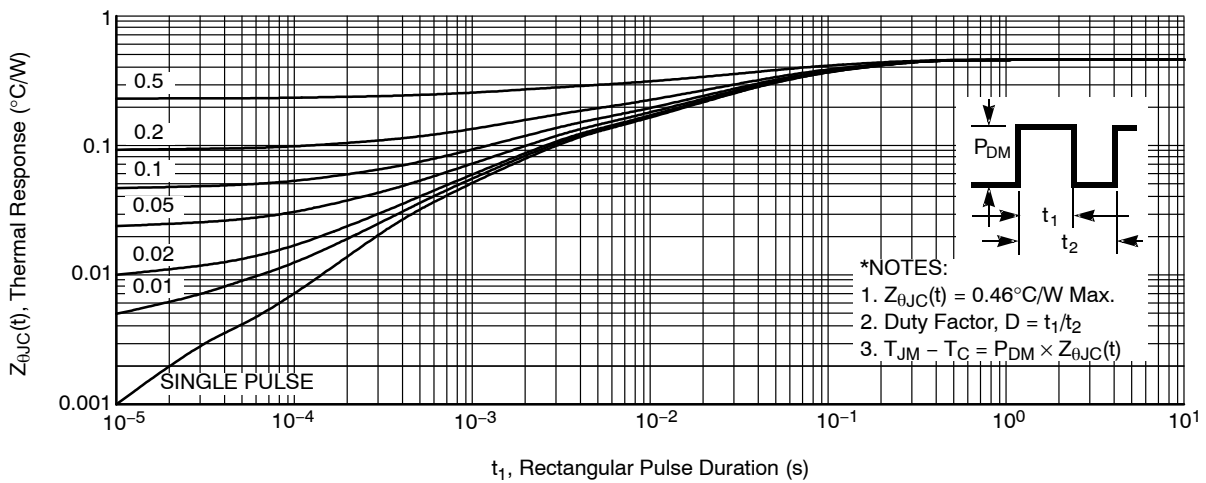


Figure 11. Transient Thermal Response Curve

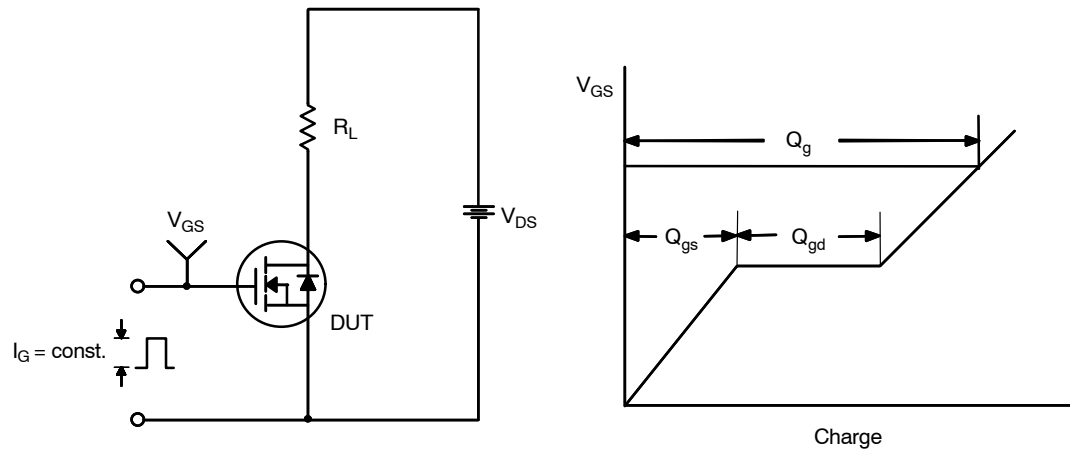


Figure 12. Gate Charge Test Circuit & Waveform

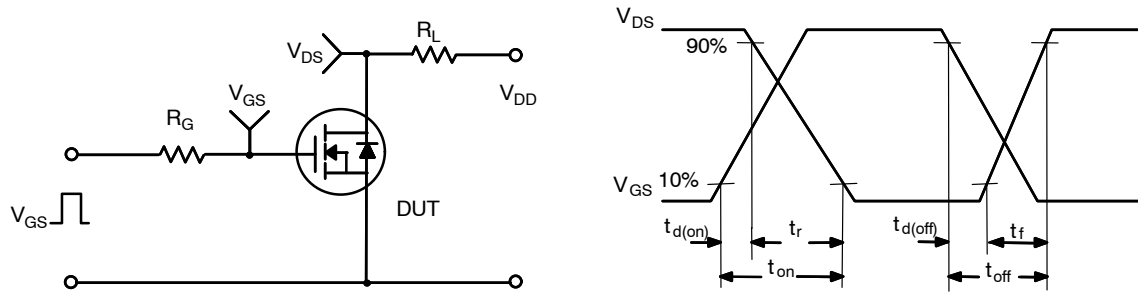


Figure 13. Resistive Switching Test Circuit & Waveforms

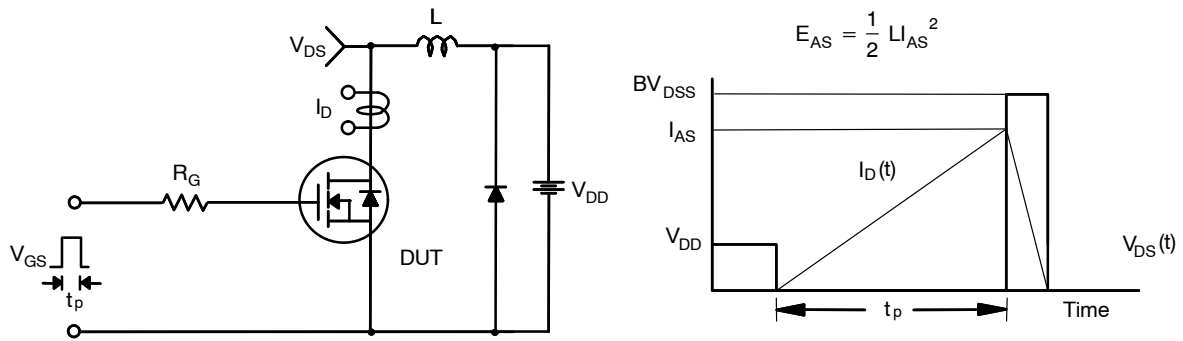
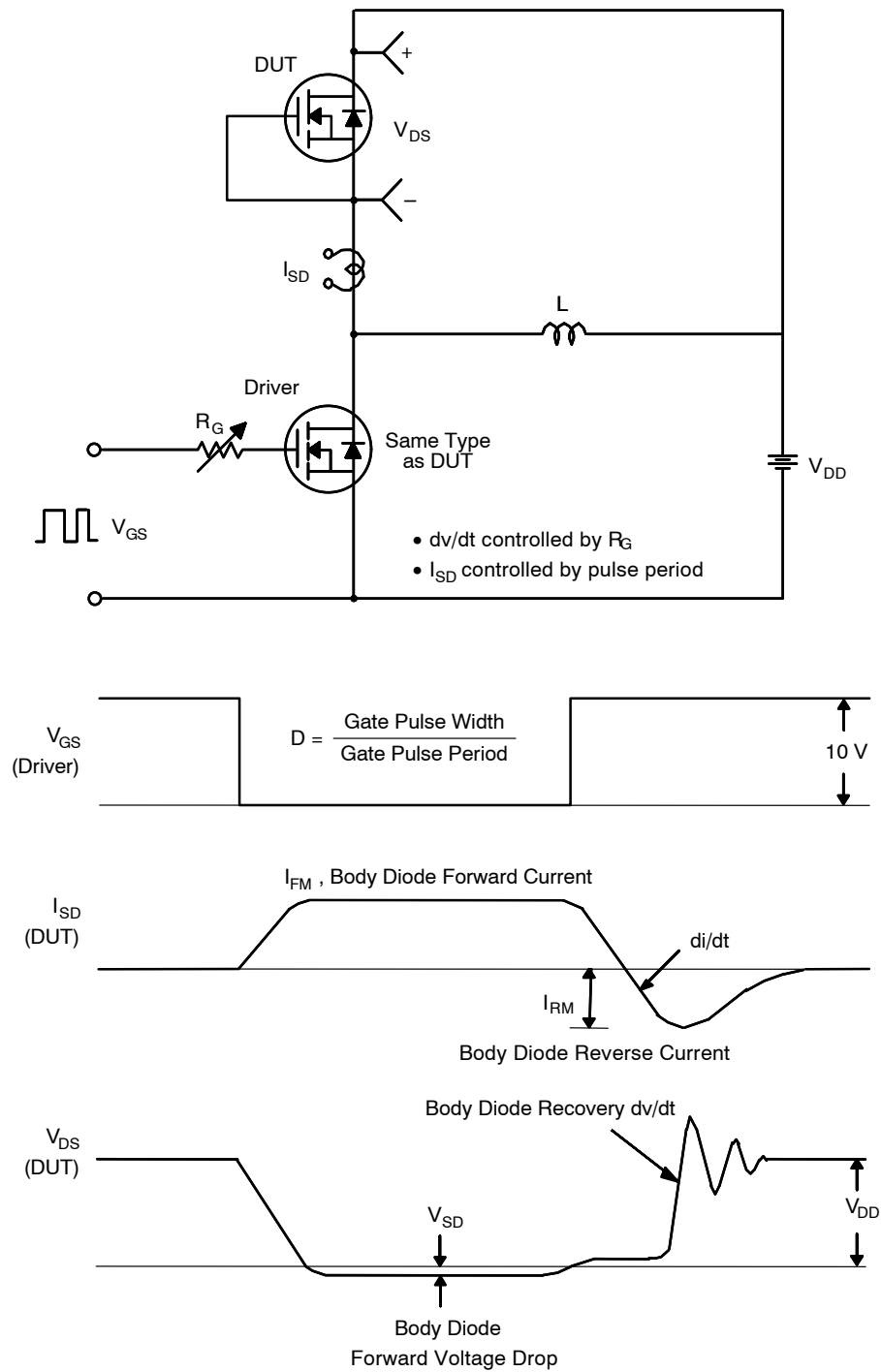


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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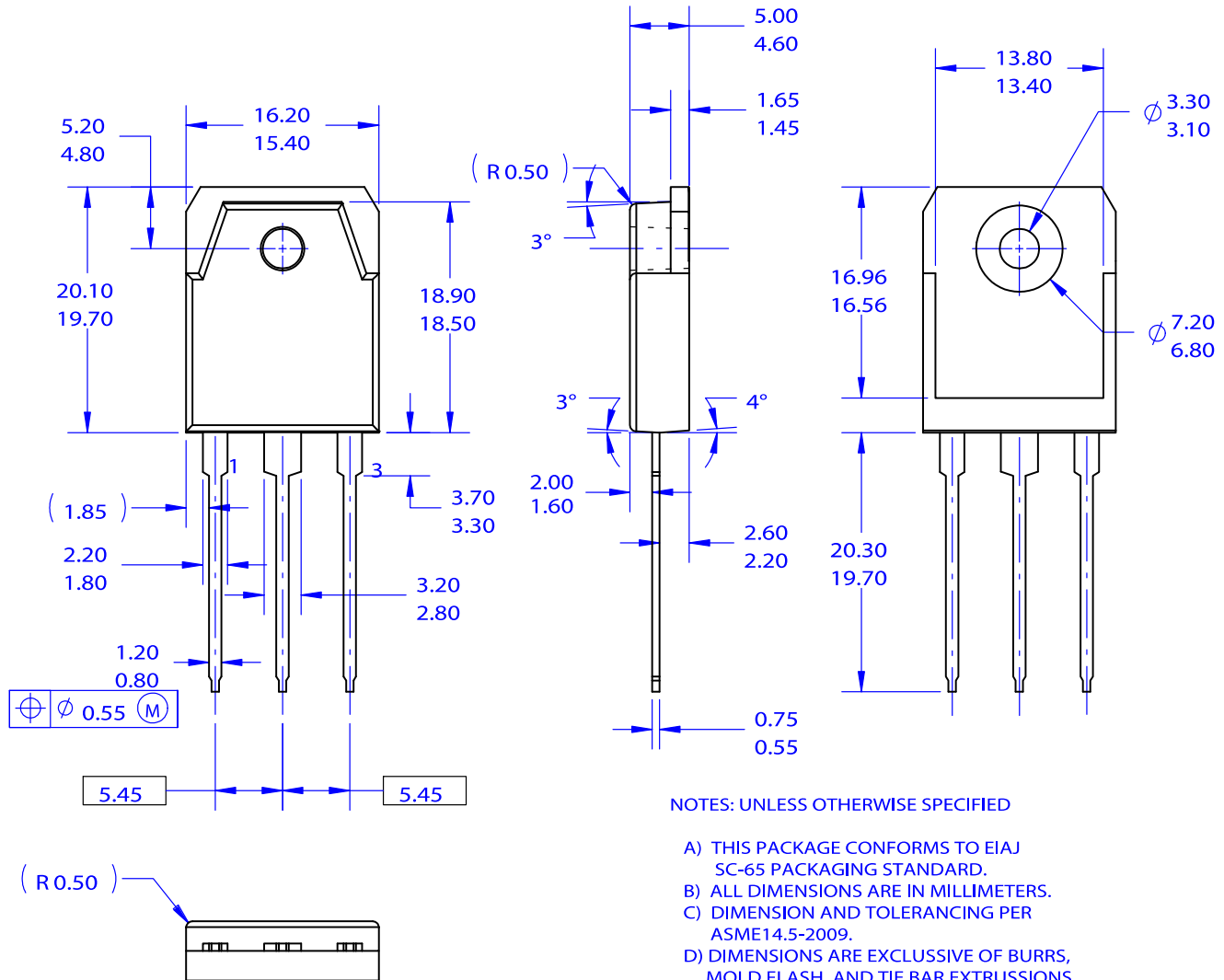
**Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**

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**TO-3P-3LD / EIAJ SC-65, ISOLATED**  
**CASE 340BZ**  
**ISSUE O**

DATE 31 OCT 2016



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